

### **Design Benefits**

- Very low switching losses
- > Fast reverse recovery
- Fast switching speed
- > Temperature independent turn-off switching losses
- > Very fast and robust intrinsic body diode

#### Key technical features

- > Best-in-class R<sub>DSon</sub> temperature dependency
- > Superior gate charge and beneficial gate charge ratio - Low power consumption of gate drivers
  - High tolerance against parasitic turn-on
- > Ultra small threshold voltage tolerance
- > Robust body diode with very low forward voltage
- > Lower leakage current up to 1200 V

## **Key applications**

- > E-vehicle charging infrastructure
- > Photovoltaic inverters
- > Switch mode power supply
- Uninterruptable power supply
- Motor drives



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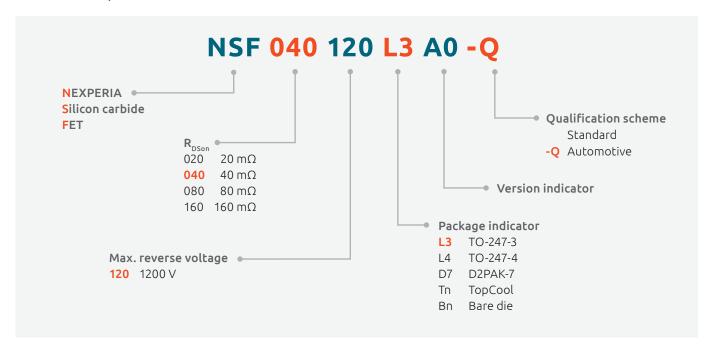
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## Product range

Type name	Package	V <sub>DS</sub> max (V)	$R_{DSon}$ typ (m $\Omega$ ) @ $T_j = 25$ °C	I <sub>D</sub> max (A) @ TC = 25 °C	T <sub>j</sub> max (°C)
NSF040120L3A0	TO-247-3	1200	40	65	175
NSF080120L3A0			80	35	
NSF040120L4A0	TO-247-4		40	65	
NSF080120L4A0			80	35	

# SiC MOSFET | Nomenclature



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